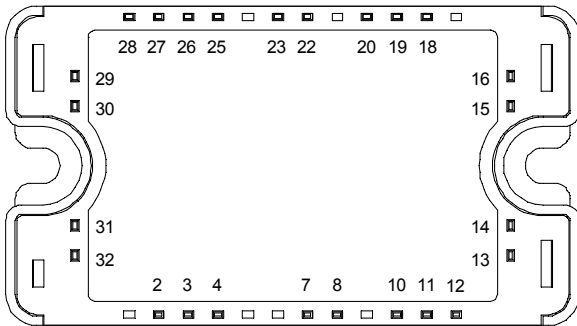
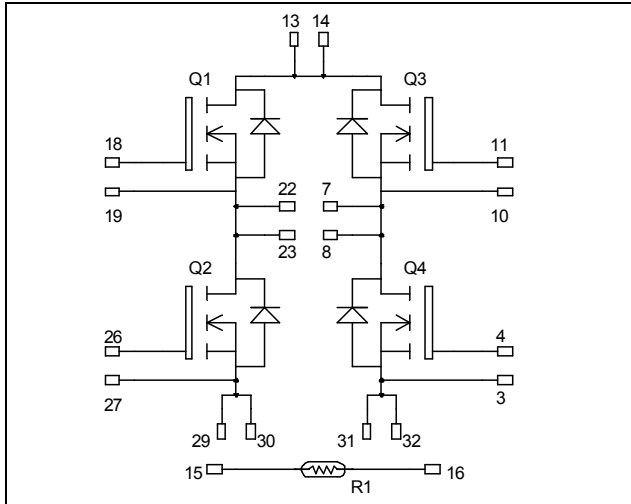


## Full - Bridge Super Junction MOSFET Power Module

$V_{DSS} = 900V$   
 $R_{DSon} = 60m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 59A \text{ @ } T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together  
 Example: 13/14 ; 29/30 ; 22/23 ...

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

### Features

- **COOLMOS** Power Semiconductors
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	900	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	59
		$T_c = 80^\circ C$	44
$I_{DM}$	Pulsed Drain current	150	
$V_{GS}$	Gate - Source Voltage	$\pm 20$	V
$R_{DSon}$	Drain - Source ON Resistance	60	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	462
$I_{AR}$	Avalanche current (repetitive and non repetitive)	8.8	A
$E_{AR}$	Repetitive Avalanche Energy	2.9	mJ
$E_{AS}$	Single Pulse Avalanche Energy	1940	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 900V$ $T_j = 25^\circ\text{C}$			200	$\mu\text{A}$
		$V_{GS} = 0V, V_{DS} = 900V$ $T_j = 125^\circ\text{C}$		1000		
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 52A$		50	60	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 6\text{mA}$	2.5	3	3.5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			200	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V; V_{DS} = 100V$ $f = 1\text{MHz}$		13.6		nF
$C_{oss}$	Output Capacitance			0.66		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 52A$		540		nC
$Q_{gs}$	Gate – Source Charge			64		
$Q_{gd}$	Gate – Drain Charge			230		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (<math>125^\circ\text{C}</math>)</b> $V_{GS} = 10V$ $V_{Bus} = 600V$ $I_D = 52A$ $R_G = 3.8\Omega$		70		ns
$T_r$	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			400		
$T_f$	Fall Time			25		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 10V; V_{Bus} = 600V$ $I_D = 52A; R_G = 3.8\Omega$		3		mJ
$E_{off}$	Turn-off Switching Energy			1.5		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 10V; V_{Bus} = 600V$ $I_D = 52A; R_G = 3.8\Omega$		4.2		mJ
$E_{off}$	Turn-off Switching Energy			1.7		

**Source - Drain diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_S$	Continuous Source current (Body diode)		$T_c = 25^\circ\text{C}$			59	A
			$T_c = 80^\circ\text{C}$			44	
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -52A$		0.8	1.2	V	
$t_{rr}$	Reverse Recovery Time	$I_S = -52A$ $V_R = 400V$ $di_s/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		920	ns	
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		60	$\mu\text{C}$	

**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit	
$R_{thJC}$	Junction to Case Thermal Resistance			0.27	$^\circ\text{C}/\text{W}$	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t = 1\text{min}, I_{isol} < 1\text{mA}, 50/60\text{Hz}$	4000			V	
$T_j$	Operating junction temperature range	-40		150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-40		125		
$T_C$	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

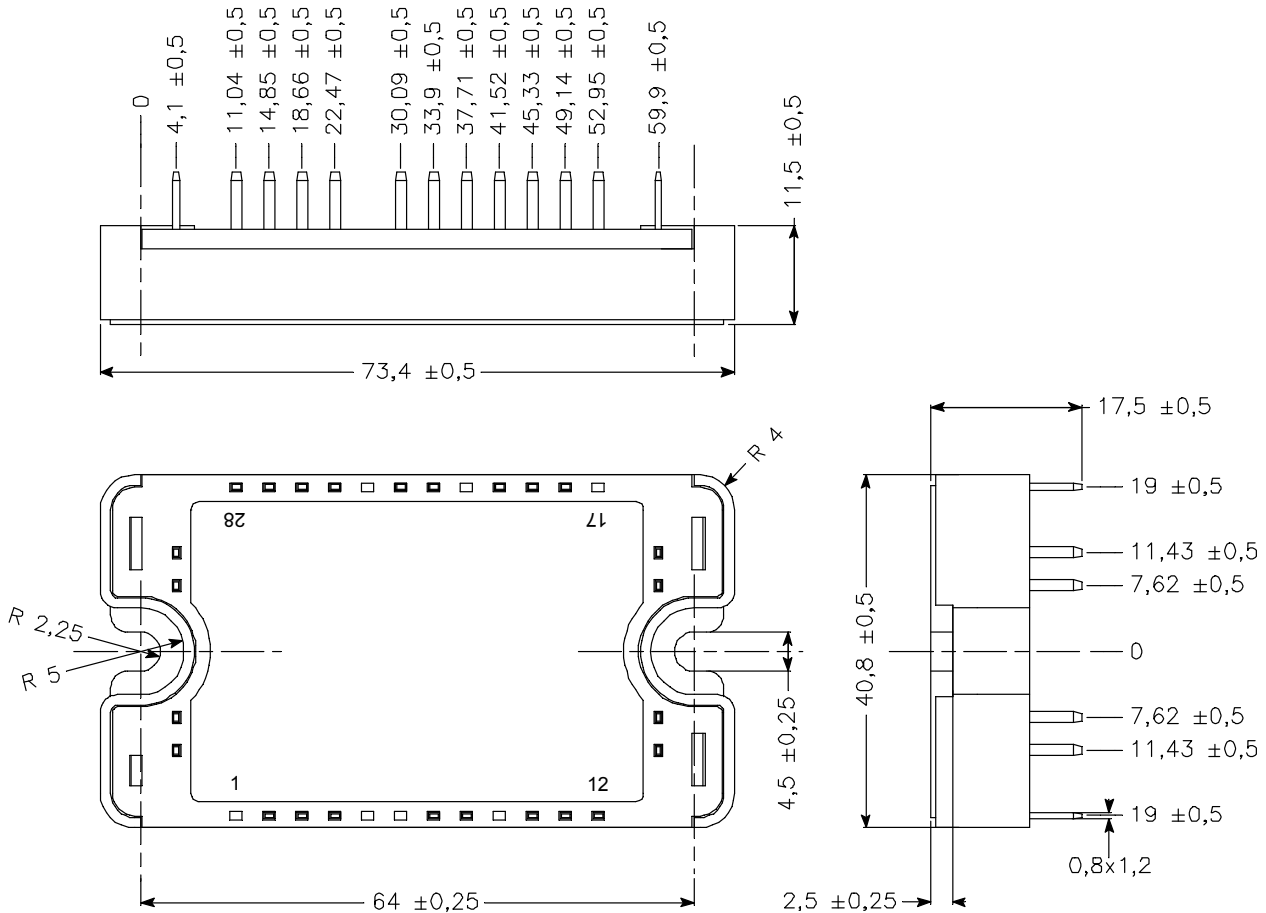
**Temperature sensor NTC** (see application note APT0406 on [www.microsemi.com](http://www.microsemi.com) for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B	T <sub>C</sub> = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

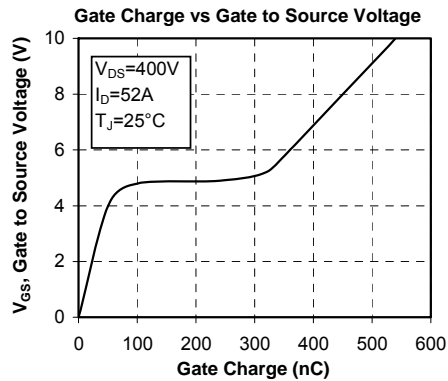
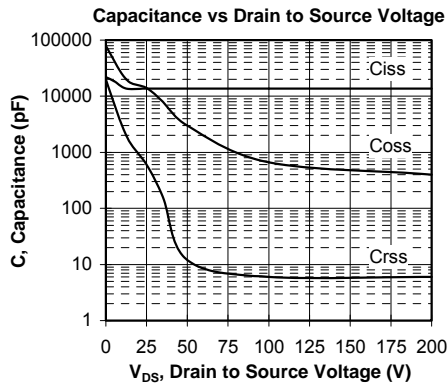
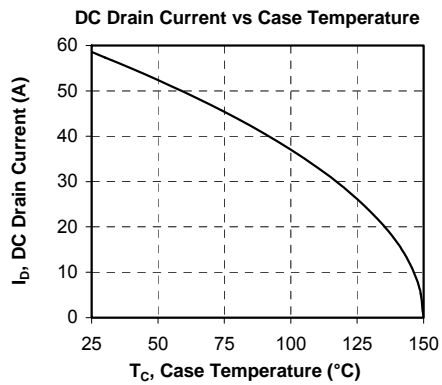
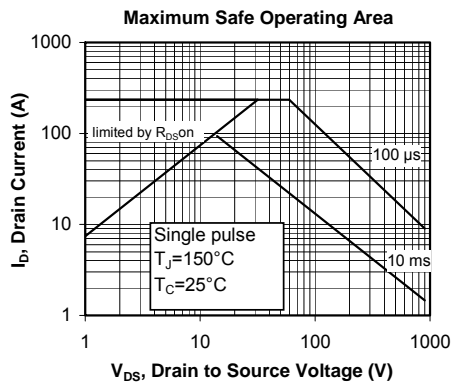
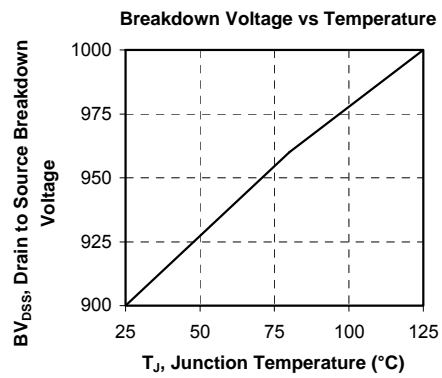
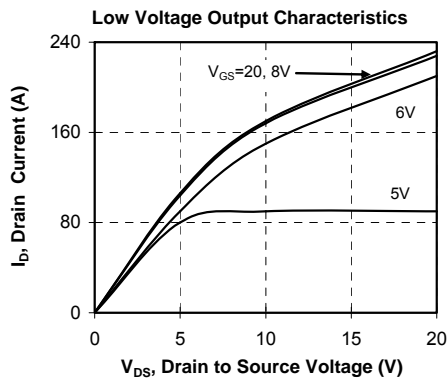
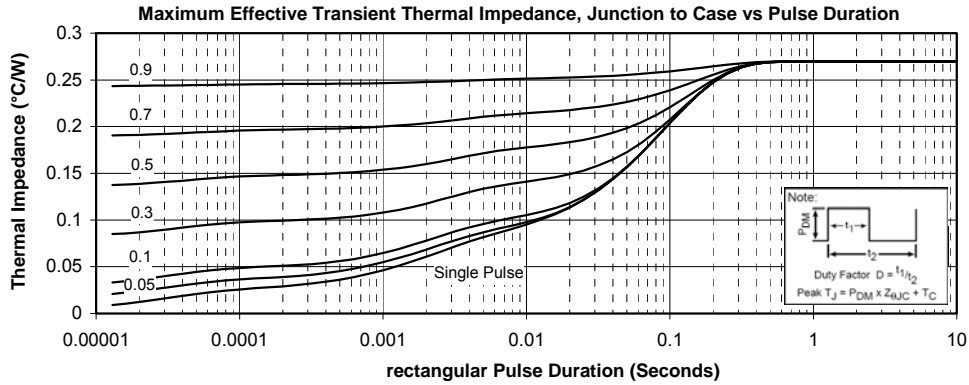
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

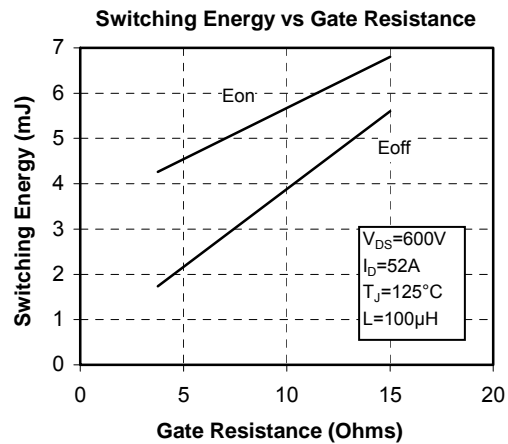
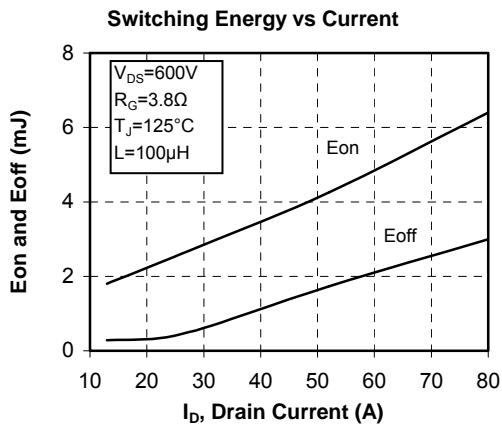
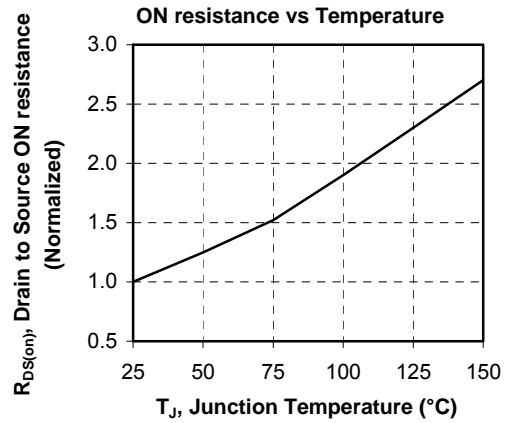
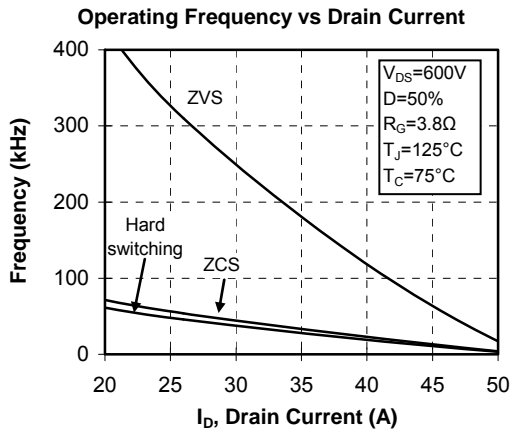
### SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical CoolMOS Performance Curve





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